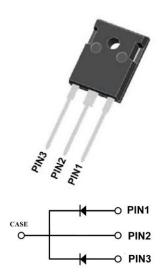
YJD112030NCTQG3



Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F(135°C)}	46A ⁽²⁾
Qc	192nC ⁽²⁾



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-247AB
 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_C=25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112030NCTQG3
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _C =25°C			49/98
Continuous forward current @ T _C =135°C	I _F	А	23/46
Continuous forward current @ T _C =155°C			15/30
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	160 ⁽¹⁾
Repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FRM}	А	92 ⁽¹⁾
Power Dissipation@ T _C =25°C	Б	107	214(1)
Power Dissipation@ T _C =110°C	P _{TOT}	W	92(1)
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	128 ⁽¹⁾
Operating junction and Storage temperature range	T_j , T_stg	°C	-55 to +175

⁽¹⁾ Per Leg, (2) Per Device





■Electrical Characteristics (Per Leg)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =15A, T _j =25°C	1.35	1.55
			I _F =15A, T _j =175°C	1.85	-
Reverse leakage current	I _R	μA	V _R =1200V, T _j =25°C	3	20
			V _R =1200V, T _j =175°C	19	-
Total capacitive charge	Q _C	nC	V_R =800V, T_j =25°C, Q_C = $\int_0^{VR} C(V) dV$	96	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	1346	-
			V _R =400V, f=1MHZ	90	-
			V _R =800V, f=1MHZ	65	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	25	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	0.70 ⁽¹⁾ 0.35 ⁽²⁾

⁽¹⁾ Per Leg, ⁽²⁾ Per Device

■Typical Characteristics (Per Leg)

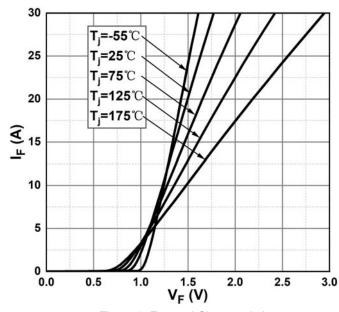


Figure 1. Forward Characteristics

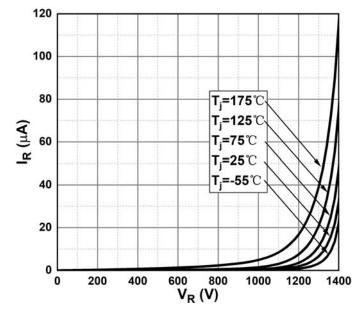
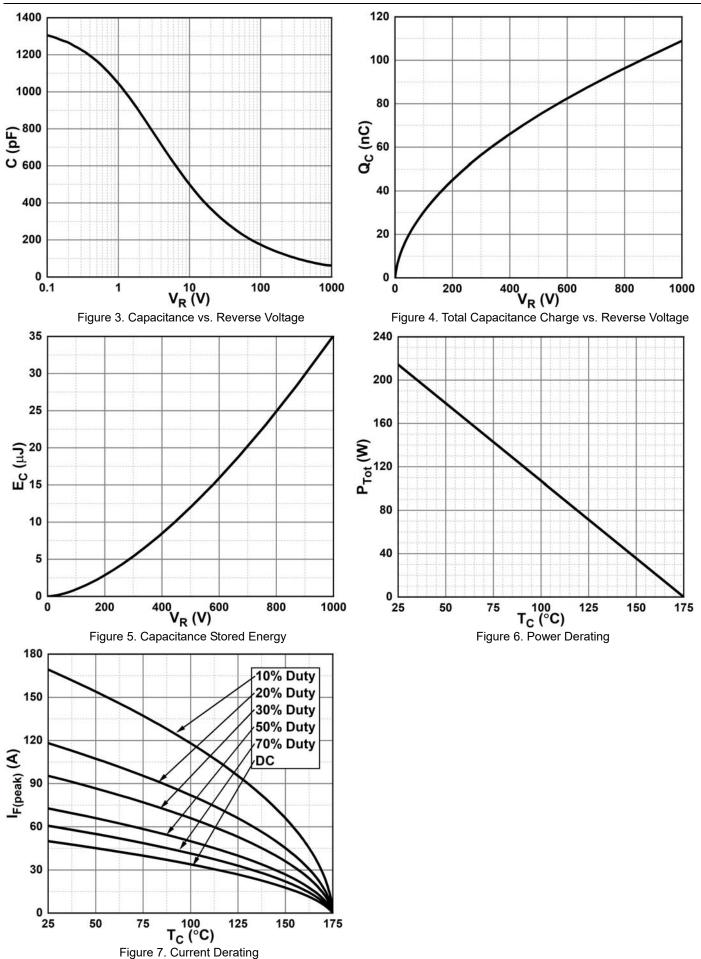


Figure 2. Reverse Characteristics









■Typical Characteristics (Device)

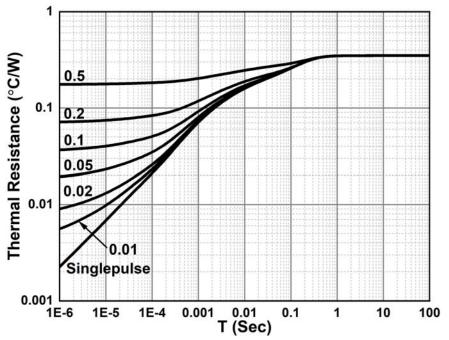


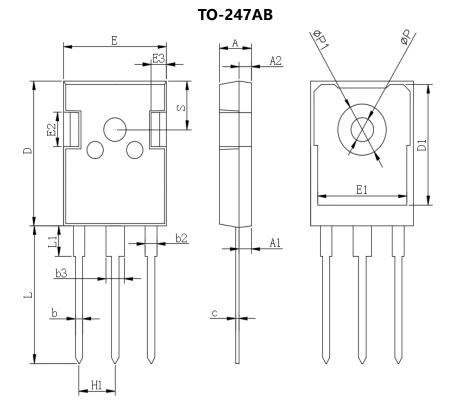
Figure 8. Transient Thermal Impedance







■Outline Dimensions



TO-247AB				
Dim	Min	Max		
Α	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.0	1.4		
b2	1.91	2.21		
С	0.5	0.7		
D	20.70	21.30		
D1	16.25	16.85		
E	15.50	16.10		
E1	13.0	13.6		
E2	4.80	5.20		
E3	2.30	2.70		
L	19.62	20.22		
L1	-	4.30		
ΦР	3.40	3.80		
ФР1	-	7.30		
S	6.15TYP			
H1	5.44TYP			
b3	2.80	3.20		



YJD112030NCTQG3



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